

# PBSS5350TH

# 50 V, 3 A PNP low VCEsat (BISS) transistor 21 June 2017

**Product data sheet** 

# 1. General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Higher efficiency leading to less heat genereation
- High temperature applications up to 175 °C
- AEC-Q101 qualified

## 3. Applications

- Power management
- DC-to-DC conversion
- Supply line switches
- Battery charger switches
- Peripheral drivers
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver

## 4. Quick reference data

Table 1. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-	-50	V
I <sub>C</sub>	collector current			-	-	-2	Α
I <sub>CM</sub>	peak collector current	pulsed	[1]	-	-	-3	Α
		single pulse; t <sub>p</sub> < 1 ms		-	-	-5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[2]	-	-	135	mΩ

- [1] Pulse conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$
- [2] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	E	emitter		В
3	С	collector	1 2 TO-236AB (SOT23)	E sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number		Package	ckage					
		Name	Description	Version				
	PBSS5350TH	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5350TH	FJ%

[1] % = placeholder for manufacturing site code

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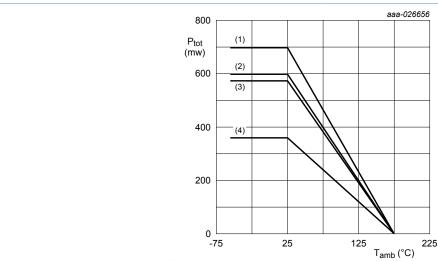
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
$V_{EBO}$	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-2	Α
I <sub>CM</sub>	peak collector current	pulsed	[1]	-	-3	Α
		single pulse; t <sub>p</sub> < 1 ms		-	-5	Α
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	360	mW
			[3]	-	575	mW
			[4]	-	600	mW
			<u>[5]</u>	-	700	mW
			[1] [2]	-	1.44	W
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Pulse conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper, 1  $\mathrm{cm}^2$
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single sided copper, 1 cm<sup>2</sup>
- (4) FR4 PCB, single sided copper, standard footprint

Fig. 1. Power derating curves for SOT23

PBSS5350TH

#### 50 V, 3 A PNP low VCEsat (BISS) transistor

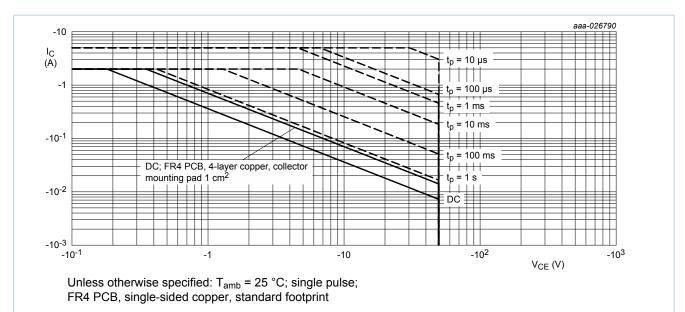


Fig. 2. Safe operating area; junction to ambient; continuous and peak drain currents as a function of collectoremitter voltage

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	-	417	K/W
			<u>[2]</u>	-	-	261	K/W
			[3]	-	-	250	K/W
			[4]	-	-	215	K/W
			[1] [5]	-	-	104	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Operated under pulse conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$

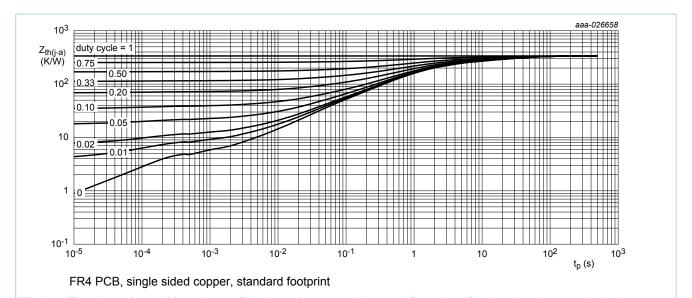


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

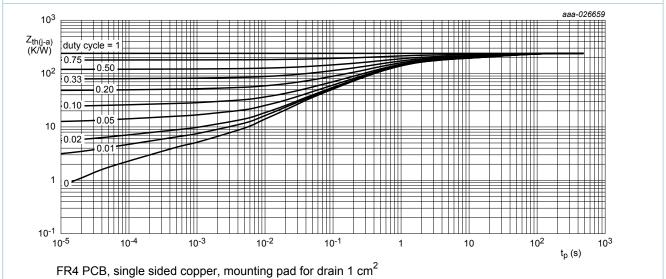


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

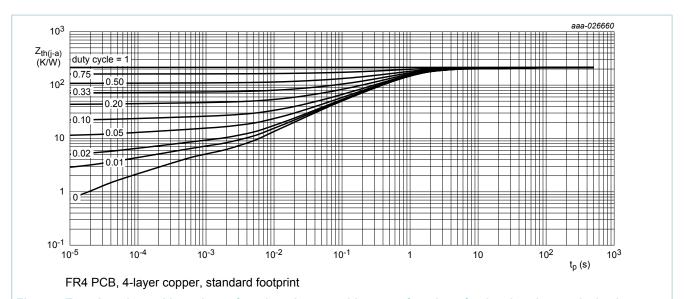


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

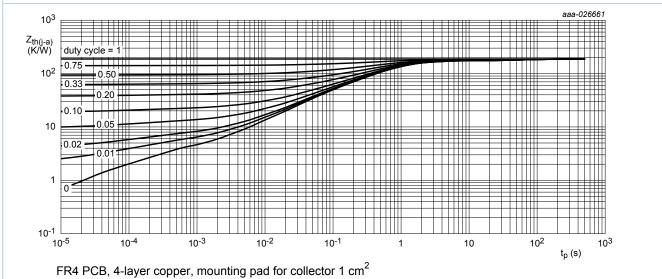


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

**Table 7. Characteristics** 

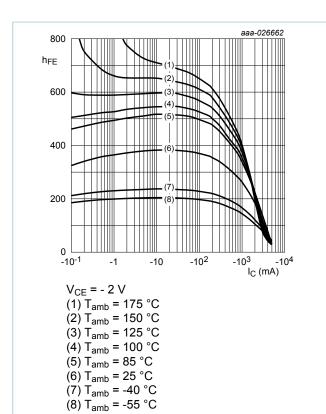
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \mu A; I_E = 0 A; T_{amb} = 25 °C$		-50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C$ = -10 mA; $I_B$ = 0 A; $T_{amb}$ = 25 °C		-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		-7	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	[1]	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	[1]	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $T_{amb}$ = 25 °C	[1]	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; $T_{amb}$ = 25 °C	[1]	130	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; $T_{amb}$ = 25 °C	[1]	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	[1]	-	-	-90	mV
		$I_C = -1 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-180	mV
		$I_C$ = -2 A; $I_B$ = -100 mA; $T_{amb}$ = 25 °C	[1]	-	-	-320	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; $T_{amb}$ = 25 °C	[1]	-	-	-270	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; $T_{amb}$ = 25 °C	[1]	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	135	mΩ
$V_{BEsat}$	base-emitter saturation	$I_C$ = -2 A; $I_B$ = -100 mA; $T_{amb}$ = 25 °C	[1]	-	-	-1.1	V
	voltage	$I_C$ = -3 A; $I_B$ = -300 mA; $T_{amb}$ = 25 °C	[1]	-	-	-1.2	V
$V_{BE}$	base-emitter voltage	$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; } T_{amb} = 25 \text{ °C}$	[1]	-	-	-1.2	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C		100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $i_e$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	35	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 

- 1200

 $V_{BE}$ (mV)

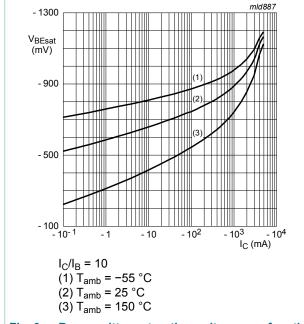
- 800



- 400 - 10  $-10^{2}$ I<sub>C</sub> (mA) V<sub>CE</sub> = −2 V (1)  $T_{amb} = -55 \, ^{\circ}C$ (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = 150 \, ^{\circ}C$ 

Base-emitter voltage as a function of collector Fig. 8. current; typical values





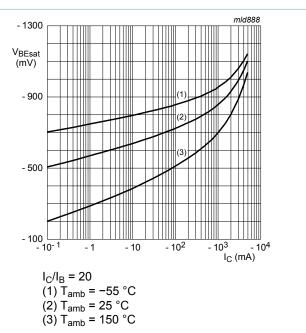


Fig. 9. collector current; typical values

Base-emitter saturation voltage as a function of Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

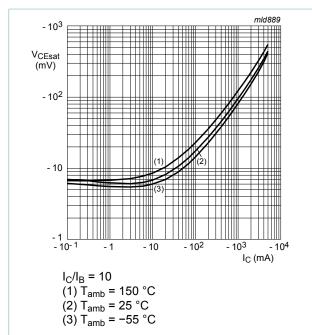


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

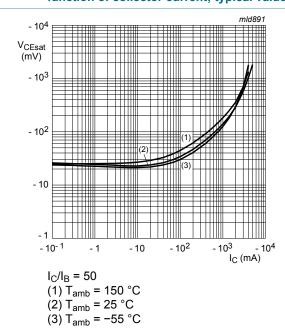


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

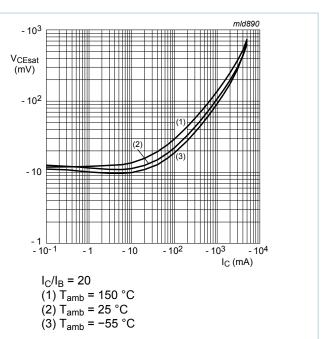


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

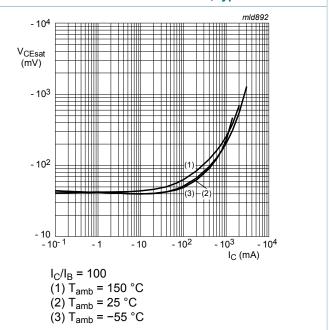
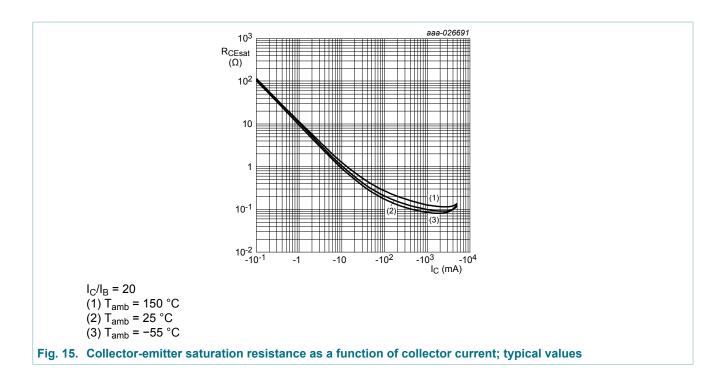


Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

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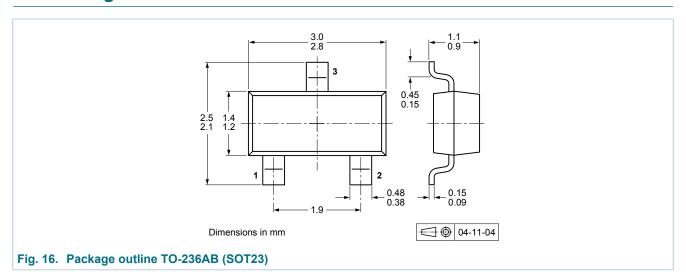


## 11. Test information

#### **Quality information**

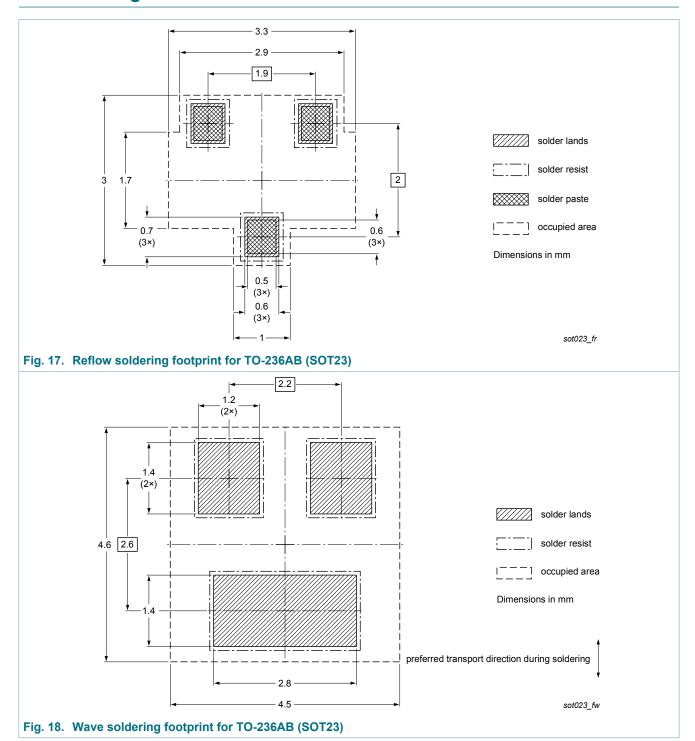
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



50 V, 3 A PNP low VCEsat (BISS) transistor

# 13. Soldering



50 V, 3 A PNP low VCEsat (BISS) transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350TH v.1	20170621	Product data sheet	-	-

#### 50 V, 3 A PNP low VCEsat (BISS) transistor

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 50 V, 3 A PNP low VCEsat (BISS) transistor

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	Features and benefits

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